

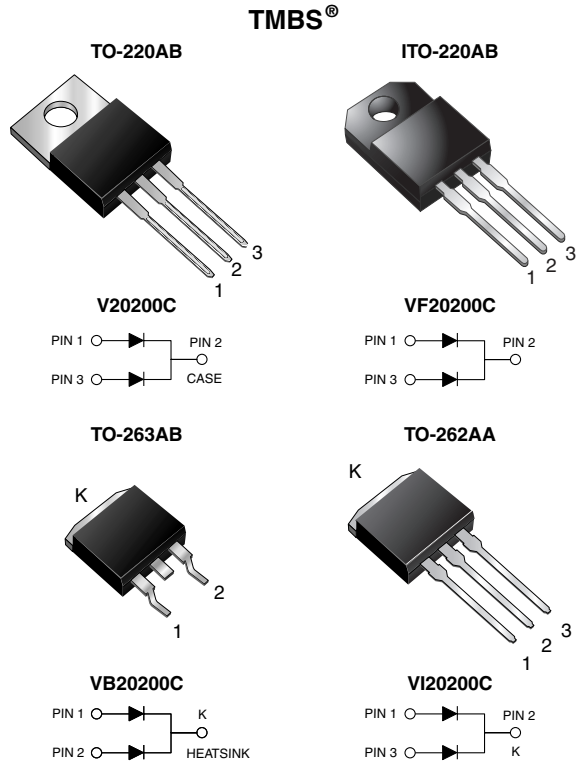


**New Product**  
**V20200C, VF20200C, VB20200C & VI20200C**

Vishay General Semiconductor

## Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.60\text{ V}$  at  $I_F = 5\text{ A}$



### FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Low thermal resistance
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB, ITO-220AB and TO-262AA package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### TYPICAL APPLICATIONS

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

### MECHANICAL DATA

**Case:** TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Epoxy meets UL 94V-0 flammability rating

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for commercial grade, meets JESD 201 class 1A whisker test

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum

### PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	200 V
$I_{FSM}$	120 A
$V_F$ at $I_F = 10\text{ A}$	0.68 V
$T_J$ max.	150 °C

### MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	V20200C	VF20200C	VB20200C	VI20200C	UNIT
Maximum repetitive peak reverse voltage	$V_{RRM}$	200				V
Maximum average forward rectified current (Fig. 1) per device per diode	$I_{F(AV)}$	20 10				A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	$I_{FSM}$	120				A
Peak repetitive reverse current at $t_p = 2\text{ }\mu\text{s}$ , 1 kHz per diode	$I_{RRM}$	0.5				A
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1\text{ min}$	$V_{AC}$	1500				V
Operating junction and storage temperature range	$T_J, T_{STG}$	- 40 to + 150				°C

<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 1.0\text{ mA}$	$T_A = 25\text{ }^\circ\text{C}$	$V_{BR}$	200 (minimum)	-	V
Instantaneous forward voltage per diode <sup>(1)</sup>	$I_F = 5\text{ A}$	$T_A = 25\text{ }^\circ\text{C}$	$V_F$	0.85	-	V
	$I_F = 10\text{ A}$	$T_A = 25\text{ }^\circ\text{C}$		1.21	1.60	
Reverse current per diode <sup>(2)</sup>	$V_R = 180\text{ V}$	$T_A = 25\text{ }^\circ\text{C}$	$I_R$	6	-	$\mu\text{A}$
		$T_A = 125\text{ }^\circ\text{C}$		3.6	-	mA
	$V_R = 200\text{ V}$	$T_A = 25\text{ }^\circ\text{C}$		-	150	$\mu\text{A}$
		$T_A = 125\text{ }^\circ\text{C}$		5.6	18	mA

**Notes:**

- (1) Pulse test: 300  $\mu\text{s}$  pulse width, 1 % duty cycle
- (2) Pulse test: Pulse width  $\leq 40\text{ ms}$

<b>THERMAL CHARACTERISTICS</b> ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)						
PARAMETER	SYMBOL	V20200C	VF20200C	VB20200C	VI20200C	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	2.8	5.0	2.8	2.8	$^\circ\text{C/W}$

<b>ORDERING INFORMATION</b> (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	V20200C-E3/4W	1.88	4W	50/tube	Tube
ITO-220AB	VF20200C-E3/4W	1.75	4W	50/tube	Tube
TO-263AB	VB20200C-E3/4W	1.37	4W	50/tube	Tube
TO-263AB	VB20200C-E3/8W	1.37	8W	800/reel	Tape and reel
TO-262AA	VI20200C-E3/4W	1.45	4W	50/tube	Tube

**RATINGS AND CHARACTERISTICS CURVES**

( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise noted)

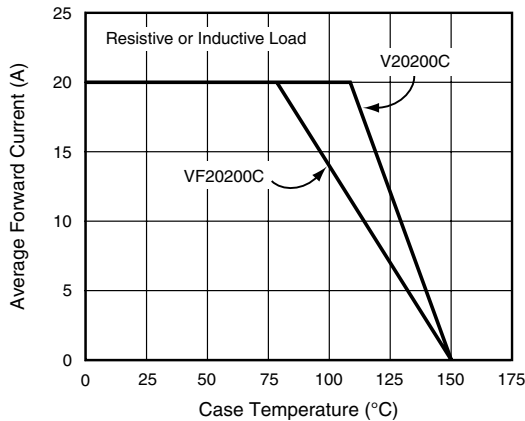


Figure 1. Maximum Forward Current Derating Curve

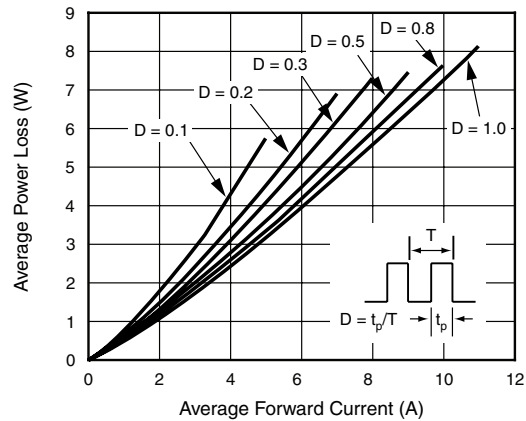


Figure 2. Forward Power Loss Characteristics Per Diode

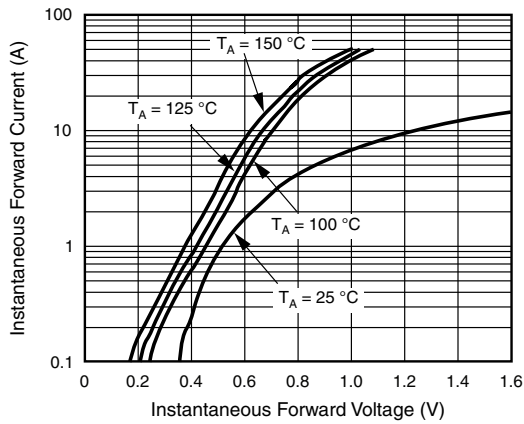


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

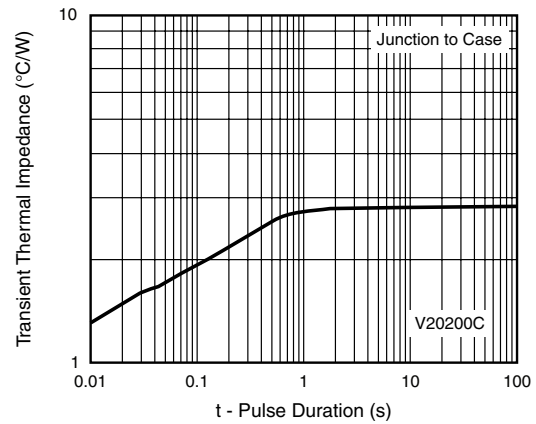


Figure 6. Typical Transient Thermal Impedance Per Diode

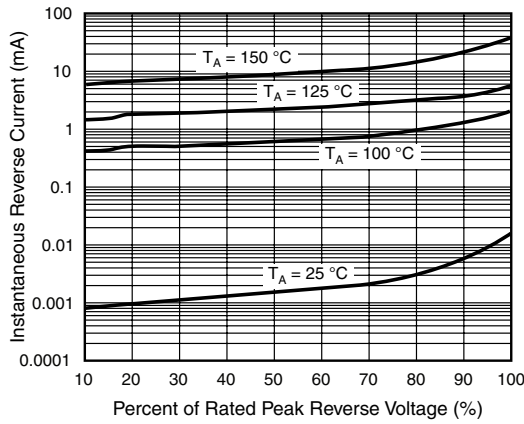


Figure 4. Typical Reverse Characteristics Per Diode

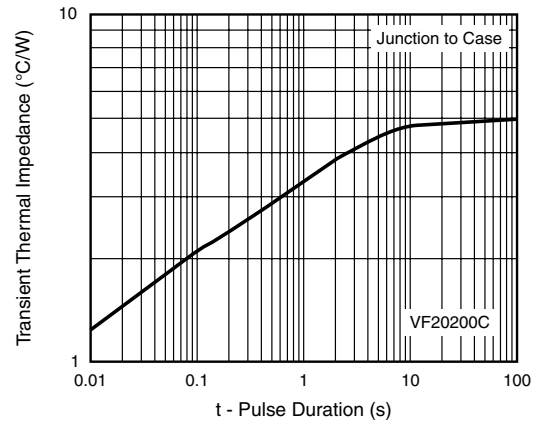


Figure 7. Typical Transient Thermal Impedance Per Diode

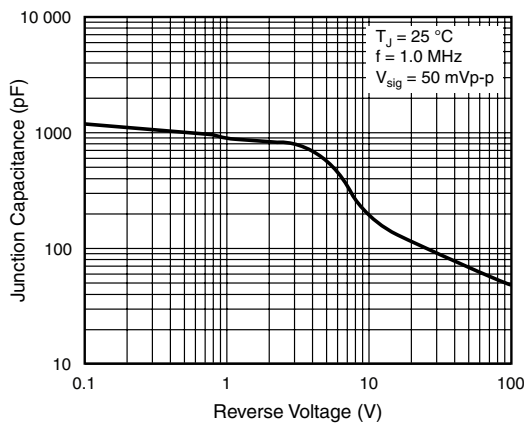


Figure 5. Typical Junction Capacitance Per Diode

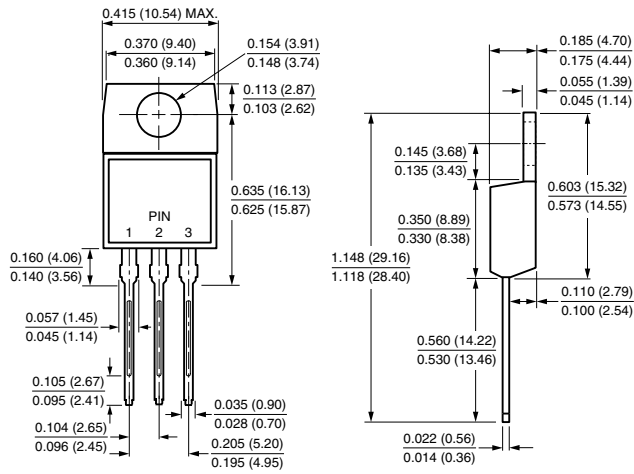
# New Product V20200C, VF20200C, VB20200C & VI20200C



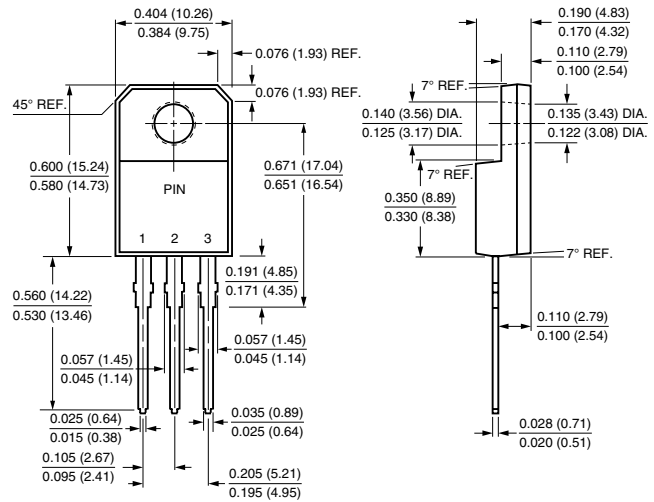
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## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

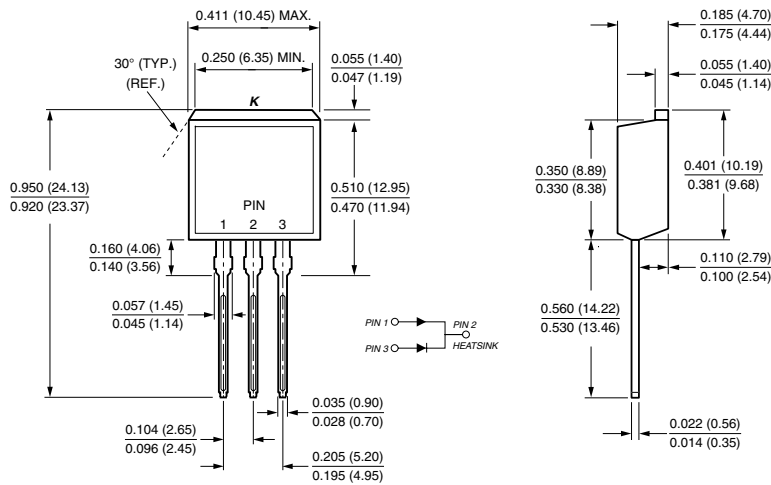
TO-220AB



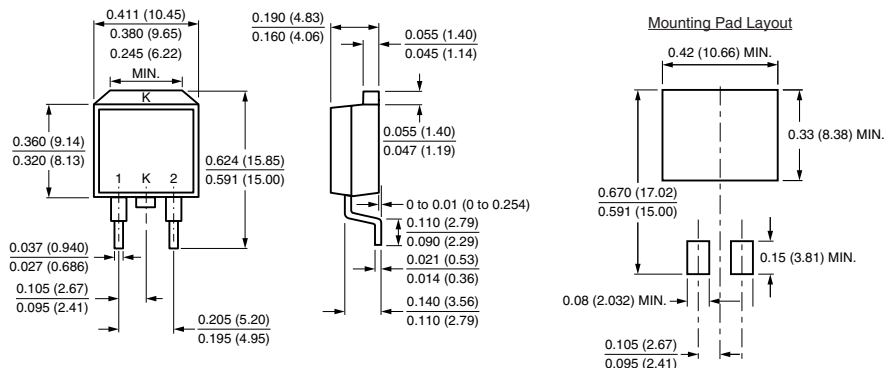
ITO-220AB



TO-262AA



TO-263AB





## Disclaimer

All product specifications and data are subject to change without notice.

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